IEEE EDS Kansai Chapter Awards 2019

■ IEEE EDS Kansai Chapter of the Year Award
Author:    Munetaka Noguchi
Title:     Channel Engineering of 4H-SiC MOSFETs Using Sulphur as a Deep Level Donor
Coauthors: T. Iwamatsu¹, H. Amishiro¹, H. Watanabe¹, K. Kita², and N. Miura¹
Affiliation: 1. Mitsubishi Electric Corporation, 2. The University of Tokyo

■ IEEE EDS Kansai Chapter MFSK Award
Author:    Takumi Kawasetsu
Title:     Flexible Tri-Axis Tactile Sensor Using Spiral Inductor and Magnetorheological Elastomer
Coauthors: T. Horii, H. Ishihara, and M. Asada
Affiliation: Osaka University

■ IEEE EDS Kansai Chapter IMFEDK Best Paper Award
Author:    Daisuke Tahara
Paper-ID:  G-6
Title:     Microstructures of ε-Ga2O3 Thin Film on (100) TiO2 Substrate by Mist Chemical Vapor Deposition
Coauthors: H. Nishinaka, Y. Arata, K. Shimazoe, and M. Yoshimoto
Affiliation: Kyoto Institute of Technology

Author:    Shan Low
Paper-ID:  G-5
Title:     Impact of SiN Capping during Ohmic Annealing on Performance of GaN-based MISHEMTs
Coauthors: S. Kawabata, J. Asubar, H. Tokuda and M. Kuzuhara
Affiliation: University of Fukui